OPE5594S

The **OPE5594S** is GaAlAs infrared emitting diode that is designed for high reliability, high radiant intensity and low forward voltage .This device is optimized for efficiency at emission wavelength 940nm and has a high radiant efficiency over a wide range of forward current. This device is packaged T1-3/4 plastic package and has medium beam angle with lensed package and cup frame.

FEATURES

- High-output power
- Medium beam angle
- High reliability and long term stability
- Available for pulse operating

APPLICATIONS

- Optical emitters
- Optical switches
- Smoke sensors
- IR remote control
- IR sound transmission

STORAGE

- Condition: 5°C~35°C,R.H.60%
- Terms: within 3 months from production date
- Remark : Once the package is opened, the products should be used within a day. Otherwise, it should be keeping in a damp proof box with desiccants.
- * Please take proper steps in order to secure reliability and safety in required conditions and environments for this device.

MAXIMUM RATINGS

-	$(T_9=25^{\circ}C)$	١
	11a-25	,

Item	Symbol	Rating	Unit	
Power Dissipation	P_{D}	150	mW	
Forward current	I_F	100	mA	
Pulse forward current	I_{FP}	1.0	A	
Reverse voltage	V_R	5.0	V	
Operating temp.	Topr.	- 25∼ +85	°C	
Soldering temp. *2	Tsol.	260.	°C	

 $^{^{*1}}$.Duty ratio = 1/100, pulse width=0.1ms.

ELECTRO-OPTICALCHARACTERISTICS

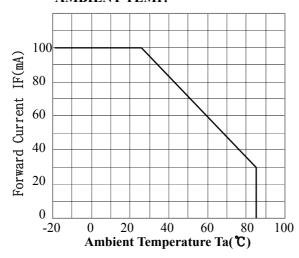
(Ta=25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward voltage	V_{F}	$I_F = 100 \text{mA}$		1.4	1.7	V
Reverse current	I_R	$V_R = 5V$			10	μA
Capacitance	Ct	f = 1 MHz		20		pF
Radiant intensity	Ie	$I_F=100mA$		60		mW/sr
Peak emission wavelength	λ_p	$I_F = 100 \text{mA}$		940		nm
Spectral bandwidth 50%	Δλ	$I_F = 100 \text{mA}$		45		nm
Half angle	ΔΘ	I _F =100mA		±10		deg.

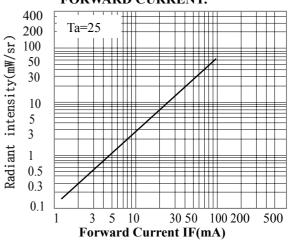
DIMENSIONS (Unit:mm)

^{*2.}Lead Soldering Temperature (2mm from case for 5sec.).

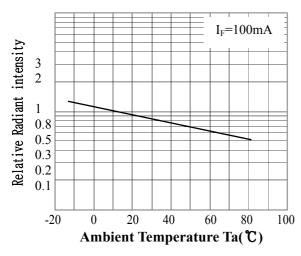
• FORWARD CURRENT Vs. AMBIENT TEMP.



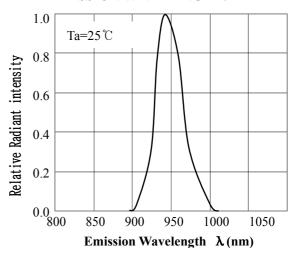
• RADIANT INTENSITY Vs. FORWARD CURRENT.



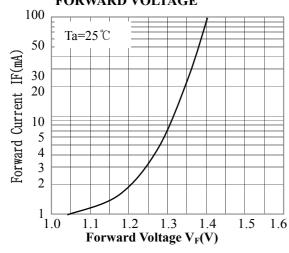
• RELATIVE RADIANT INTENSITY Vs. AMBIENT TEMP.



• RELATIVE RADIANT INTENSITY Vs. EMISSION WAVELENGTH.



• FORWARD CURRENT Vs. FORWARD VOLTAGE



• ANGULAR DISPLACEMENT Vs RELATIVE RADIANT INTENSITY

